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FQP46N15

N-Channel QFET® MOSFET

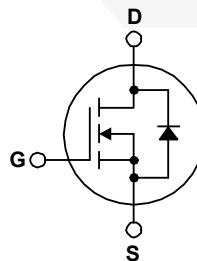
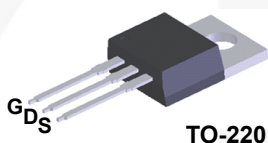
150 V, 45.6 A, 42 mΩ

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 45.6 A, 150 V, $R_{DS(on)} = 42 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 22.6 \text{ A}$
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 100 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FQP46N15	Unit
V _{DSS}	Drain-Source Voltage	150	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	45.6	A
		32.2	A
I _{DM}	Drain Current - Pulsed (Note 1)	182.4	A
V _{GSS}	Gate-Source Voltage	± 25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	650	mJ
I _{AR}	Avalanche Current (Note 1)	45.6	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	21	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	210	W
		1.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	°C

Thermal Characteristics

Symbol	Parameter	FQP46N15	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP46N15	FQP46N15	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	150	--	--	V
$\Delta BV_{DSS} / \Delta T$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.16	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 120\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 22.8\text{ A}$	--	0.033	0.042	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 22.8\text{ A}$	--	33	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2500	3250	pF
C_{oss}	Output Capacitance		--	520	670	pF
C_{rss}	Reverse Transfer Capacitance		--	100	130	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}, I_D = 45.6\text{ A},$ $R_G = 25\ \Omega$	--	35	80	ns
t_r	Turn-On Rise Time		--	320	650	ns
$t_{d(off)}$	Turn-Off Delay Time		--	210	430	ns
t_f	Turn-Off Fall Time		--	200	410	ns
Q_g	Total Gate Charge	$V_{DS} = 120\text{ V}, I_D = 45.6\text{ A},$ $V_{GS} = 10\text{ V}$	--	85	110	nC
Q_{gs}	Gate-Source Charge		--	15	--	nC
Q_{gd}	Gate-Drain Charge		--	41	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	45.6	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	182.4	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 45.6\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 45.6\text{ A},$	--	130	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$	--	0.55	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = 0.52\text{ mH}, I_{AS} = 45.6\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 45.6\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

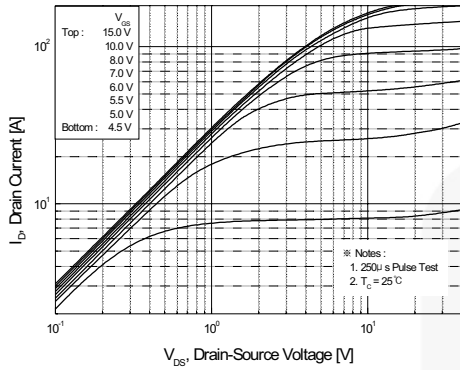


Figure 1. On-Region Characteristics

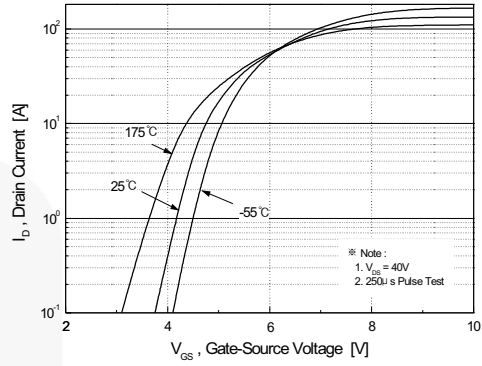


Figure 2. Transfer Characteristics

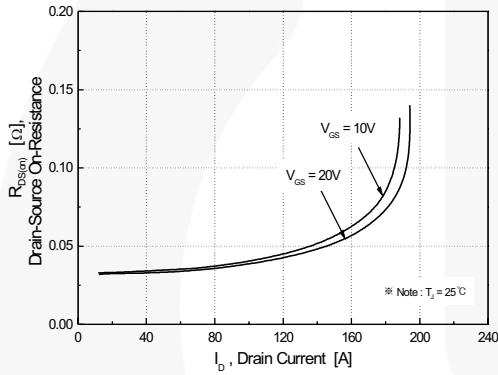


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

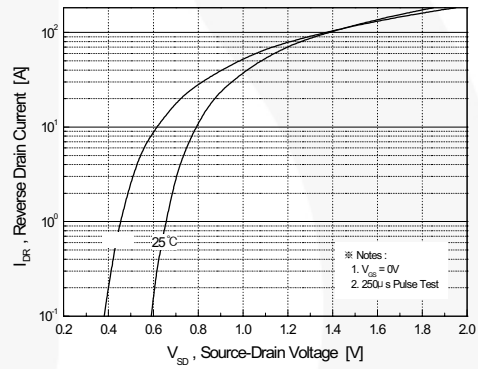


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

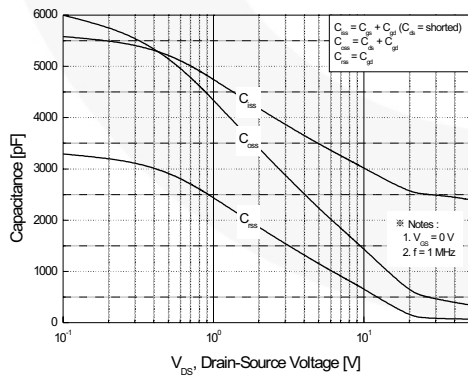


Figure 5. Capacitance Characteristics

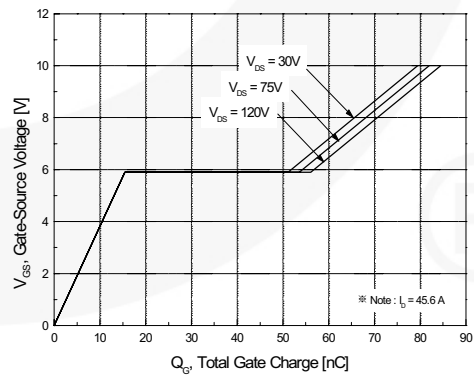


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

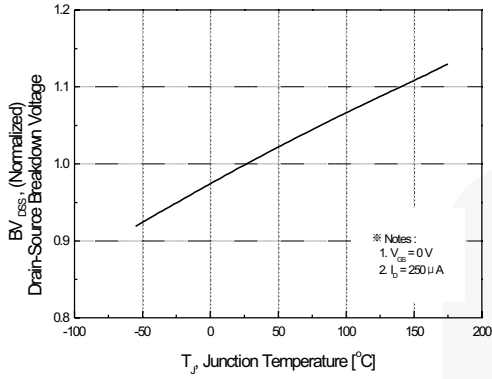


Figure 7. Breakdown Voltage Variation vs. Temperature

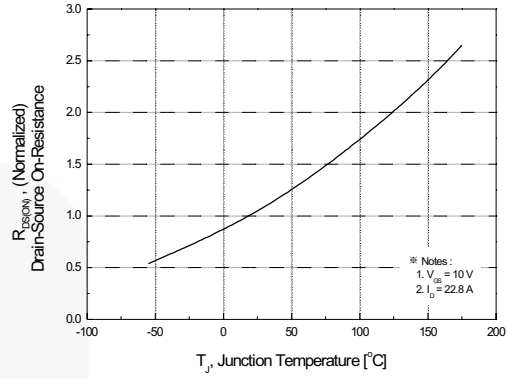


Figure 8. On-Resistance Variation vs. Temperature

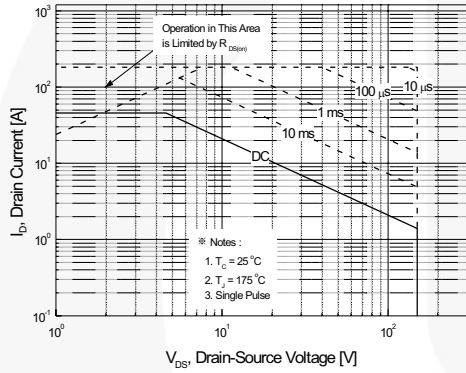


Figure 9. Maximum Safe Operating Area

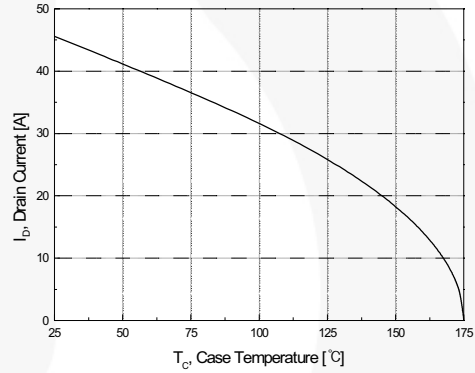


Figure 10. Maximum Drain Current vs. Case Temperature

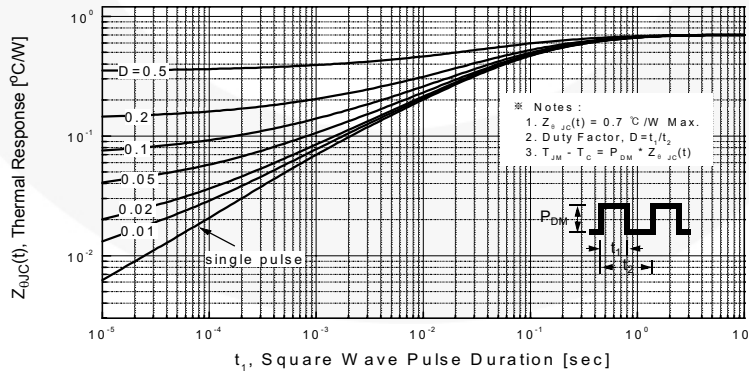


Figure 11. Transient Thermal Response Curve



Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

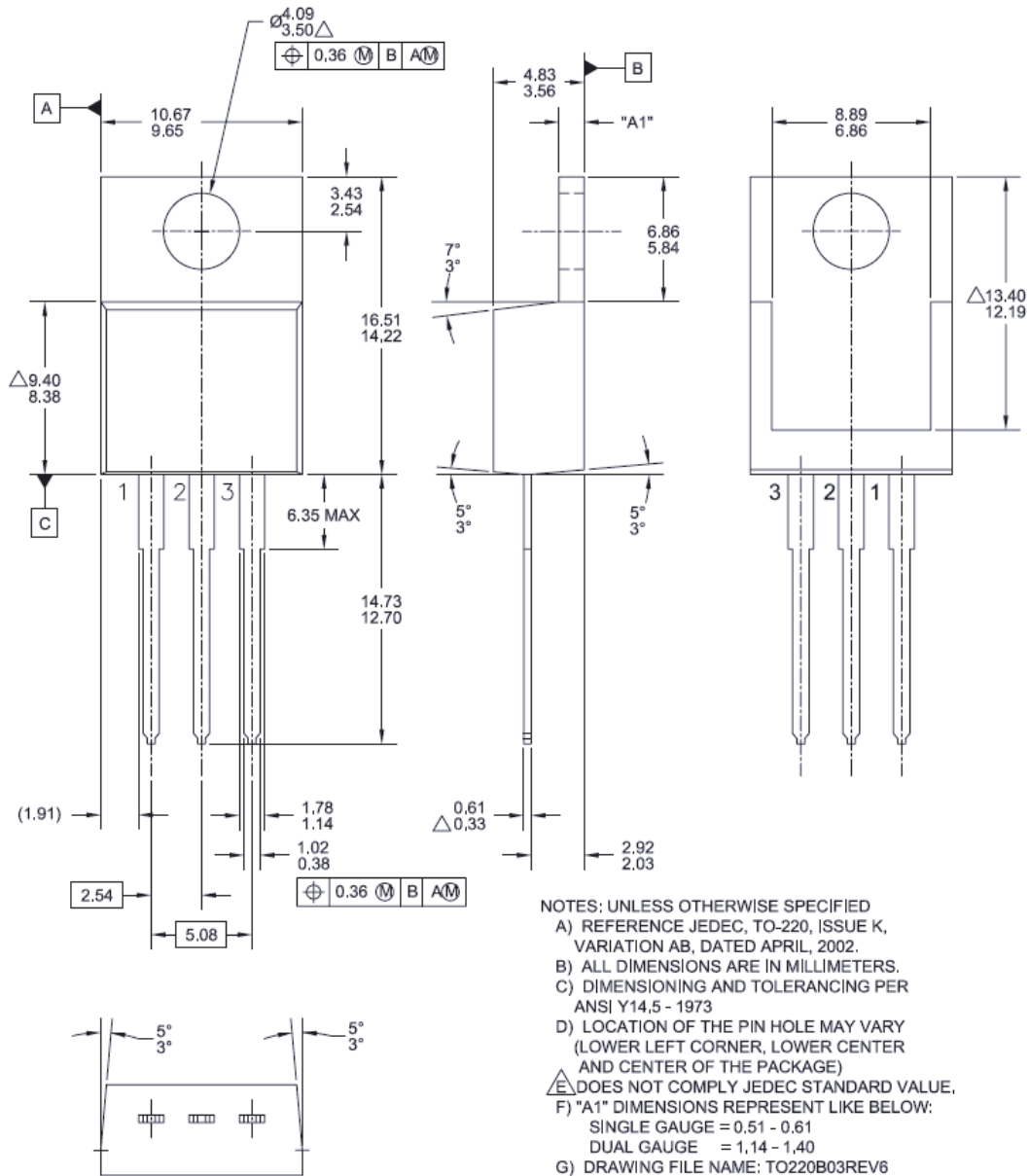


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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